2N5038 & 2N5039



NPN High Power Silicon Transistor

Rev. V3

Features

- Available in JAN, JANTX, JANTXV per MIL-PRF-19500/439
- TO-3 (TO-204AA) Package
- Ideal for Use in Switching Regulators, Inverters, Power Amplifiers and Oscillators



Electrical Characteristics (T_A = +25°C unless otherwise specified)

Parameter	Test Conditions	Symbol	Units	Min.	Max.
Collector - Emitter Breakdown Voltage	I _C = 200 mA dc, 2N5038 I _C = 200 mA dc, 2N5039	V _{(BR)CEO}	V dc	90 75	_
Collector - Base Cutoff Current	V _{CE} = 150 V dc, 2N5038 V _{CE} = 125 V dc, 2N5039	I _{CBO}	μA dc	_	1.0 1.0
Emitter - Base Cutoff Current	V _{EB} = 5.0 V dc	I _{EBO}	μA dc	<u>—</u>	100
Collector - Emitter Cutoff Current	V _{CE} = 100 V dc, V _{BE} = -1.5 V dc, 2N5038 V _{CE} = 85 V dc, V _{BE} = -1.5 V dc, 2N5039	I _{CEX1}	μA dc	_	5.0 5.0
Collector - Emitter Cutoff Current	V _{CE} = 70 V dc, 2N5038 V _{CE} = 55 V dc, 2N5039	I _{CEO}	μA dc	_	1.0 1.0
		I			
Forward Current Transfer Ratio	$I_{C} = 0.5 \text{ A dc}, V_{CE} = 5 \text{ Vdc} 2\text{N}5038$ $2\text{N}5039$ $I_{C} = 2.0 \text{ A dc}, V_{CE} = 5 \text{ Vdc} 2\text{N}5038$ $2\text{N}5039$ $I_{C} = 12 \text{ A dc}, V_{CE} = 5 \text{ Vdc} 2\text{N}5038$ $I_{C} = 10 \text{ A dc}, V_{CE} = 5 \text{ Vdc} 2\text{N}5039$	h _{FE}	-	50 30 50 30 15	200 150
Collector - Emitter Saturation Voltage	I _C = 12 A dc, I _B = 1.2 A dc 2N5038 I _C = 10 A dc, I _B = 1.0 A dc 2N5039 I _C = 20 A dc, I _B = 5.0 A dc Both	V _{CE(sat)1}	V dc	_	1.0 1.0 2.5
Emitter - Base Breakdown Voltage	I _E = 25 mA dc	$V_{(BR)EBO}$	V dc	7.0	_
Emitter - Base Saturation Voltage	I _C = 20 A dc, I _B = 5.0 A dc	V _{BE(sat)}	V dc	_	3.3
Base - Emitter Voltage (nonsaturated)	I_C = 12 A dc, V_{CE} = 5.0 V dc 2N5038 I_C = 10 A dc, V_{CE} = 5.0 V dc 2N5039	V _{BE}	V dc		1.8 1.8

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Parameter	Test Conditions	Symbol	Units	Min.	Max.	
Collector - Emitter Cutoff Current	$T_A = +150^{\circ}\text{C}$ $V_{CE} = 100 \text{ V dc}, V_{BE} = -1.5 \text{ V dc}, 2N5038$ $V_{CE} = 85 \text{ V dc}, V_{BE} = -1.5 \text{ V dc}, 2N5039$	I _{CEX2}	μA dc		100 100	
Forward Current Transfer Ratio	$T_A = -55^{\circ}C$ $V_{CE} = 5 \text{ V dc}, I_C = 12 \text{ A dc}, 2N5038$ $V_{CE} = 5 \text{ V dc}, I_C = 10 \text{ A dc}, 2N5039$	h _{FE4}	-	10 10		
Dynamic Characteristics						
Magnitude of Small-Signal Short-Circuit Forward Current Transfer Ratio	I _C = 2 A dc, V _{CE} = 10 V dc, f = 5 MHz	h _{FE}		12	48	
Open Circuit Output Capacitance	$V_{CB} = 10 \text{ V dc}, I_E = 0 \text{ A dc},$ $100 \text{ kHz} \le f \le 1 \text{ MHz}$	C _{obo}	pF	_	500	

Switching Characteristics	Symbol	Max. Value
$V_{CC} = 30 \pm 2.0 \text{V dc}$; $I_{C} = 12 \text{ A dc}$; $I_{B1} = 1.2 \text{ A dc } 2\text{N}5038$	t _{on}	0.5 μS
$V_{CC} = 30 \pm 2.0 \text{Vdc}$; $I_C = 10 \text{ A dc}$; $I_{B1} = 1.0 \text{ A dc } 2\text{N}5039$	t _{on}	0.5 μS
$V_{CC} = 30 \pm 2.0 \text{Vdc}$; $I_C = 12 \text{ A dc}$; $I_{B1} = -I_{B2} = 1.2 \text{ A dc } 2\text{N}5038$	t _{off}	2.0 μS
$V_{CC} = 30 \pm 2.0 \text{Vdc}$; $I_C = 10 \text{ A dc}$; $I_{B1} = -I_{B2} = 1.0 \text{ A dc } 2\text{N}5039$	t _{off}	2.0 μS



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Absolute Maximum Ratings (T_A = +25°C unless otherwise specified)

Ratings	Symbol	Value
Collector - Emitter Voltage 2N5038 2N5039	V _{CEO}	90 V dc 75 V dc
Collector - Base Voltage 2N5038 2N5039	V _{CBO}	150 V dc 125 V dc
Emitter - Base Voltage	V _{EBO}	7.0 V dc
Base Current	I _B	5.0 A dc
Collector Current	I _C	20 A dc
Total Power Dissipation @ $T_C = +25^{\circ}C^{(1)}$	P _T	140 W
Operating & Storage Temperature Range	T _J , T _{STG}	-65°C to +200°C

Thermal Characteristics

Characteristics	Symbol	Max. Value
Thermal Resistance, Junction to Case (2)	$R_{ heta JC}$	1.25°C/W

Safe Operating Area				
DC Tests:	T _C = +25 °C, 1Cycle, t = 1.0 s			
Test 1:	$V_{CE} = 28 \text{ V dc}, I_{C} = 5.0 \text{ A dc}$			
Test 2:	$V_{CE} = 45 \text{ V dc}, I_{C} = 0.9 \text{ A dc}$			
Test 3:	$V_{CE} = 7.0 \text{ V dc}, I_{C} = 20 \text{ A dc},$			
Test 4:	$V_{CE} = 90 \text{ V dc}, I_{C} = 0.23 \text{ A dc}, 2N5038$			
Test 4:	$V_{CE} = 75 \text{ V dc}, I_{C} = 0.32 \text{ A dc}, 2N5039$			

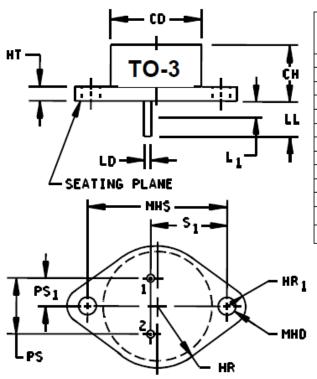
⁽¹⁾ Derate linearly 800 mW / °C for $T_A > + 25$ °C (2) See figure 4 of MIL-PRF-19500/439 for thermal impedance curve.



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Outline Drawing (TO-3)



Symbol		Notes			
	Inc	Inches		Millimeters	
	Min	Max	Min	Max	
CD		.875		22.22	
CH	.270	.380	6.86	9.65	
HR	.495	.525	12.57	13.33	4
HR ₁	.131	.188	3.33	4.78	4
HT	.060	.135	1.52	3.43	
LD	.038	.053	0.97	1.35	4, 6
LL	.312	.500	7.92	12.70	
L ₁		.050		1.27	6
MHD	.151	.165	3.84	4.19	4
MHS	1.177	1.197	29.90	30.40	
PS	.420	.440	10.67	11.18	3
PS ₁	.205	.225	5.21	5.72	3
S1	.655	.675	16.64	17.15	

NOTES:

- 1. Dimensions are in inches.
- 2. Millimeters are given for general information only.
- 3. These dimensions should be measured at points .050 .055 inch (1.27 mm 1.40 mm) below seating plane. When gauge is not used, measurement will be made at seating plane.
- 4. Two places.
- The seating plane of the header shall be flat within .001 inch (0.03 mm) inside a .930 inch (23.62 mm) diameter circle on the center of the header and flat within .001 inch (0.03 mm) concave to .006 inch (0.15 mm) convex overall.
- 6. Lead diameter shall not exceed twice LD within L₁.
- 7. Terminal 1 is emitter; terminal 2 is base; case is collector.

FIGURE 1. Physical dimensions, (TO-3).

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Outline Drawing

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